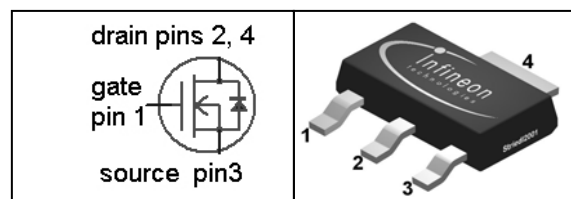


**SIPMOS<sup>®</sup> Small-Signal-Transistor**
**Features**

- N-channel
- Depletion mode
- $dv/dt$  rated

**Product Summary**

$V_{DS}$	200	V
$R_{DS(on),max}$	3.5	$\Omega$
$I_{DSS,min}$	0.14	A

**SOT-223**


Type	Package	Ordering Code	Tape and Reel Information	Marking
BSP149	SOT-223	Q67000-S071	E6327: 1000 pcs/reel	BSP149

**Maximum ratings, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_A=25\text{ }^\circ\text{C}$	0.66	A
		$T_A=70\text{ }^\circ\text{C}$	0.53	
Pulsed drain current	$I_{D,pulse}$	$T_A=25\text{ }^\circ\text{C}$	2.6	
Reverse diode $dv/dt$	$dv/dt$	$I_D=0.66\text{ A}$ , $V_{DS}=160\text{ V}$ , $di/dt=200\text{ A}/\mu\text{s}$ , $T_{j,max}=150\text{ }^\circ\text{C}$	6	kV/ $\mu\text{s}$
Gate source voltage	$V_{GS}$		$\pm 20$	V
ESD sensitivity (HBM) as per MIL-STD 883			Class 1	
Power dissipation	$P_{tot}$	$T_A=25\text{ }^\circ\text{C}$	1.8	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 150	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1			55/150/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics**

Thermal resistance, junction - soldering point (pin 4)	$R_{thJS}$		-	-	25	K/W
SMD version, device on PCB	$R_{thJA}$	minimal footprint	-	-	115	
		6 cm <sup>2</sup> cooling area <sup>1)</sup>	-	-	70	

**Electrical characteristics, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=-3\text{ V}, I_D=250\text{ }\mu\text{A}$	200	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=3\text{ V}, I_D=400\text{ }\mu\text{A}$	-2.1	-1.4	-1	
Drain-source leakage current	$I_{D(off)}$	$V_{DS}=200\text{ V}, V_{GS}=-3\text{ V}, T_j=25\text{ }^\circ\text{C}$	-	-	0.1	$\mu\text{A}$
		$V_{DS}=200\text{ V}, V_{GS}=-3\text{ V}, T_j=125\text{ }^\circ\text{C}$	-	-	5	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	10	nA
Saturated drain current	$I_{DSS}$	$V_{GS}=0\text{ V}, V_{DS}=10\text{ V}$	140	-	-	mA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=0\text{ V}, I_D=70\text{ mA}$	-	1.7	3.5	$\Omega$
		$V_{GS}=10\text{ V}, I_D=660\text{ mA}$	-	1.0	1.8	
Transconductance	$g_{fs}$	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=0.48\text{ A}$	0.4	0.8	-	S

<sup>1)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (single layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=-3\text{ V}, V_{DS}=25\text{ V}, f=1\text{ MHz}$	-	326	430	pF
Output capacitance	$C_{oss}$		-	41	55	
Reverse transfer capacitance	$C_{rss}$		-	17	25	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=100\text{ V}, V_{GS}=-2\dots 7\text{ V}, I_D=0.50\text{ A}, R_G=6\ \Omega$	-	5.1	7.7	ns
Rise time	$t_r$		-	3.4	5.1	
Turn-off delay time	$t_{d(off)}$		-	45	68	
Fall time	$t_f$		-	21	31	

**Gate Charge Characteristics**

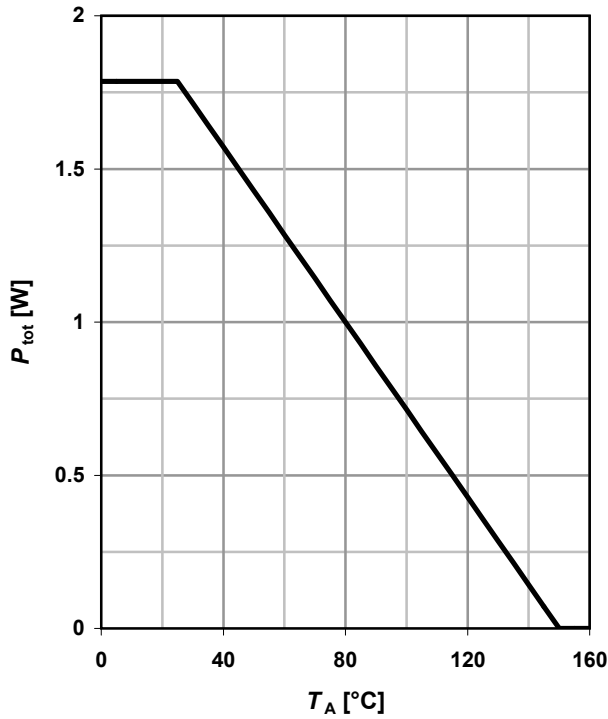
Gate to source charge	$Q_{gs}$	$V_{DD}=160\text{ V}, I_D=0.05\text{ A}, V_{GS}=-3\text{ to }5\text{ V}$	-	0.74	1.0	nC
Gate to drain charge	$Q_{gd}$		-	5.6	8.4	
Gate charge total	$Q_g$		-	11	14	
Gate plateau voltage	$V_{plateau}$		-	0.16	-	V

**Reverse Diode**

Diode continuous forward current	$I_S$	$T_A=25\text{ }^\circ\text{C}$	-	-	0.66	A
Diode pulse current	$I_{S,pulse}$		-	-	2.6	
Diode forward voltage	$V_{SD}$	$V_{GS}=-3\text{ V}, I_F=0.66\text{ A}, T_J=25\text{ }^\circ\text{C}$	-	0.9	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=100\text{ V}, I_F=0.5\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$	-	42	65	ns
Reverse recovery charge	$Q_{rr}$		-	60	90	nC

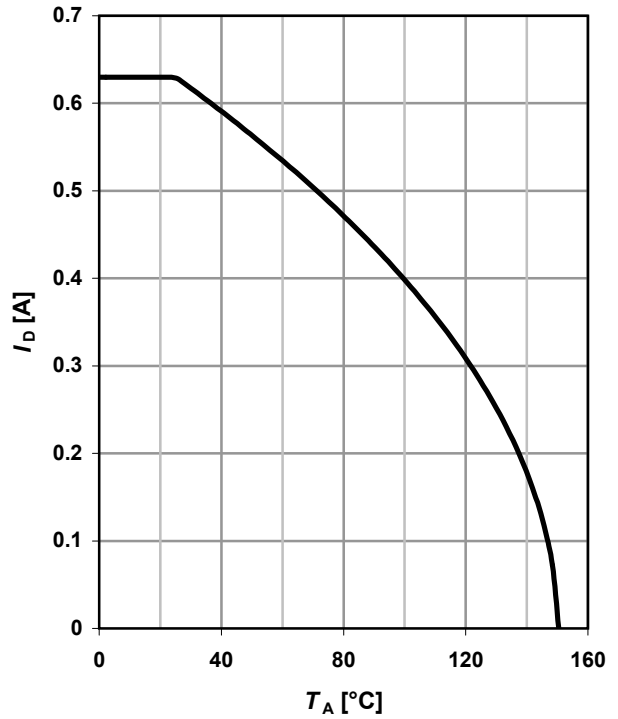
**1 Power dissipation**

$P_{tot}=f(T_A)$



**2 Drain current**

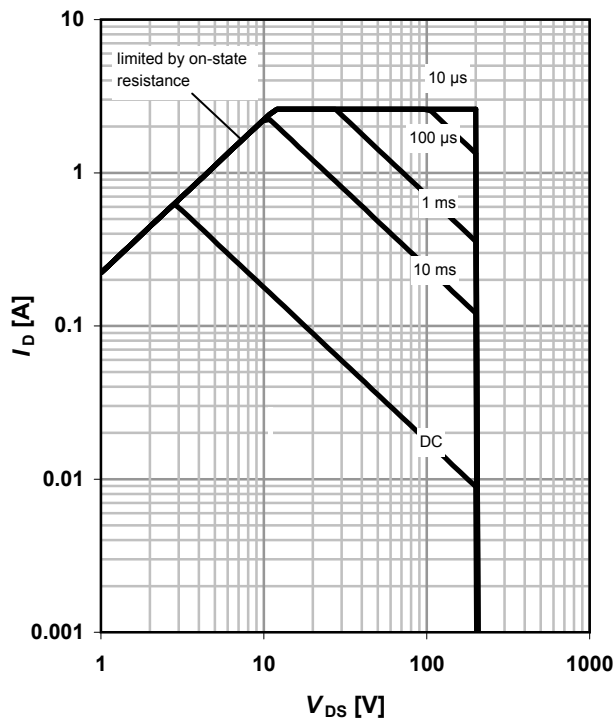
$I_D=f(T_A); V_{GS} \geq 10\text{ V}$



**3 Safe operation area**

$I_D=f(V_{DS}); T_A=25\text{ °C}; D=0$

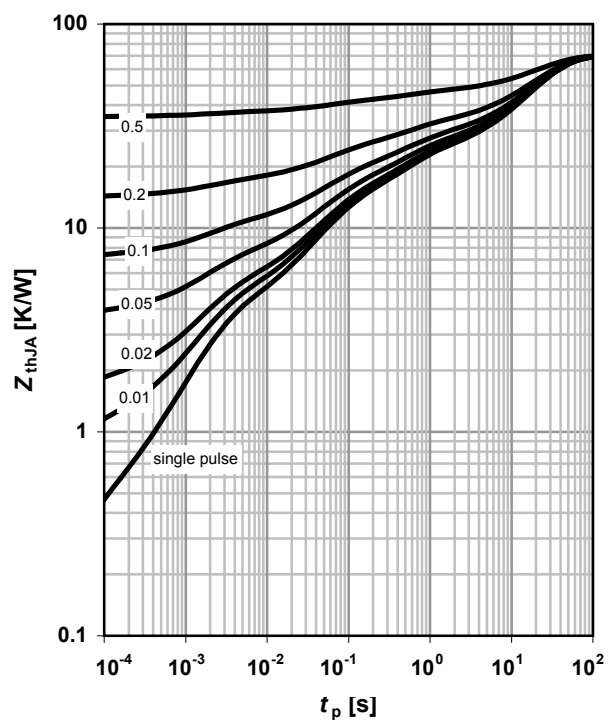
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJA}=f(t_p)$

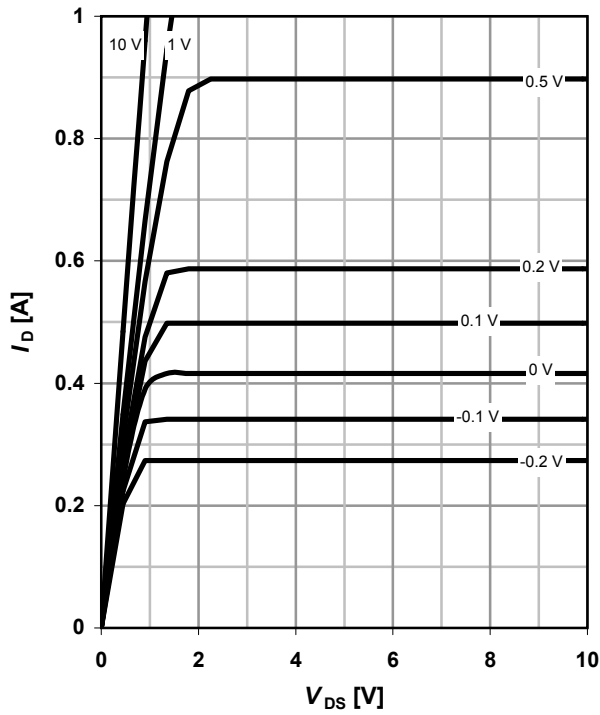
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

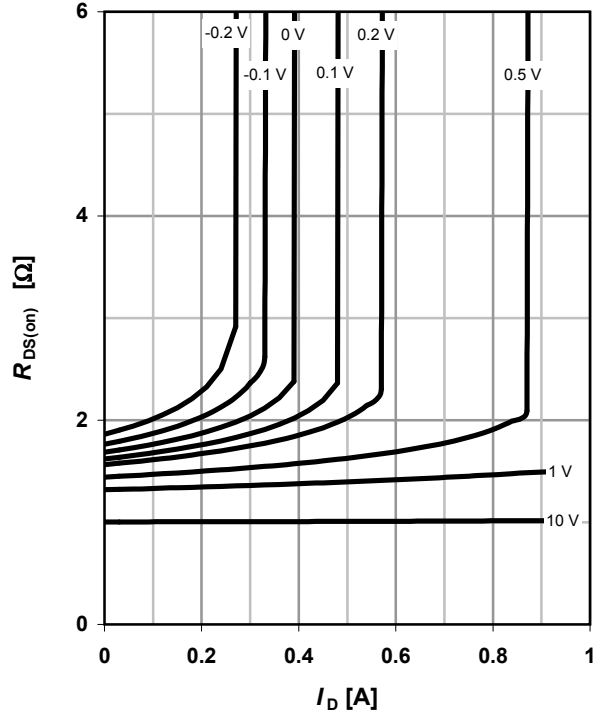
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

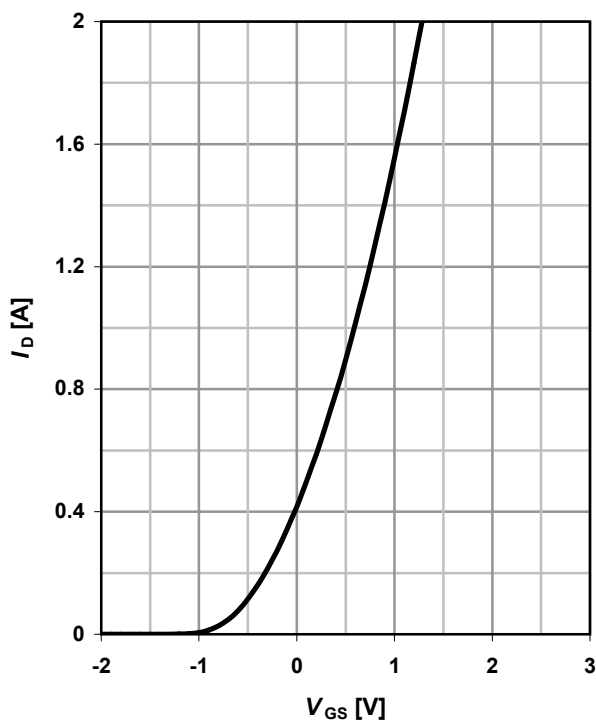
$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

parameter:  $V_{GS}$



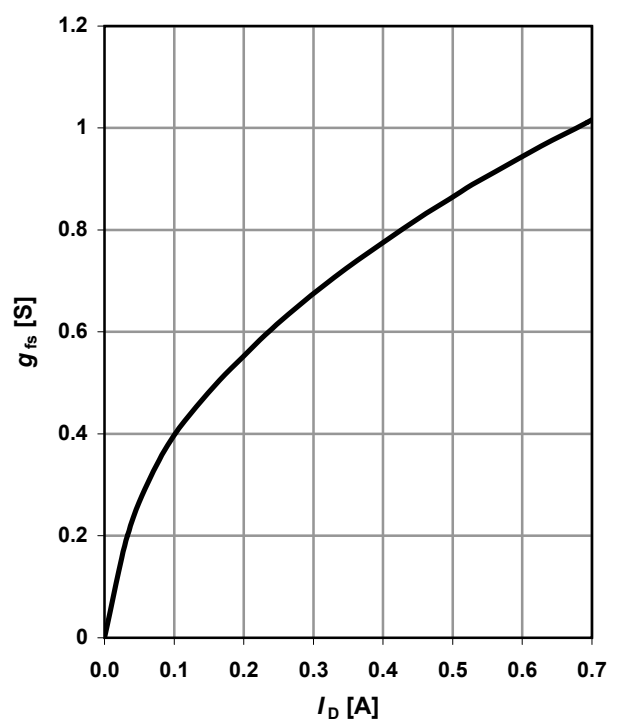
**7 Typ. transfer characteristics**

$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$



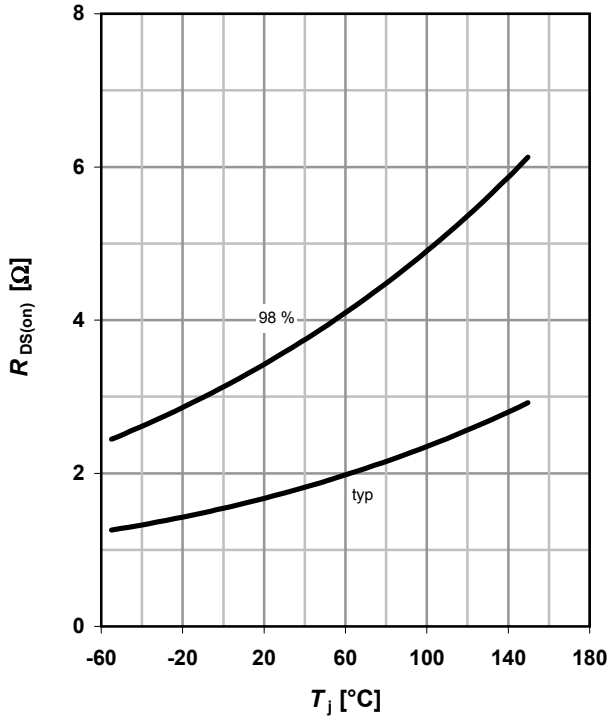
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



**9 Drain-source on-state resistance**

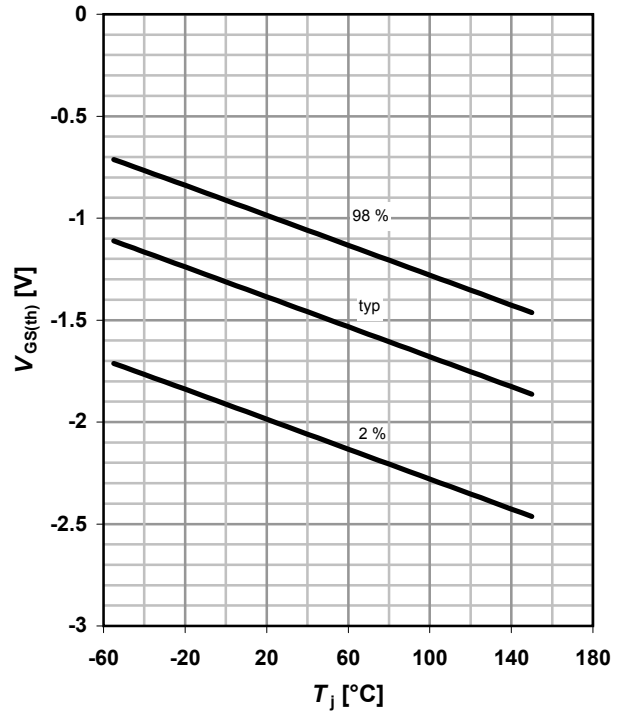
$R_{DS(on)} = f(T_j); I_D = 0.07 \text{ A}; V_{GS} = 0 \text{ V}$



**10 Typ. gate threshold voltage**

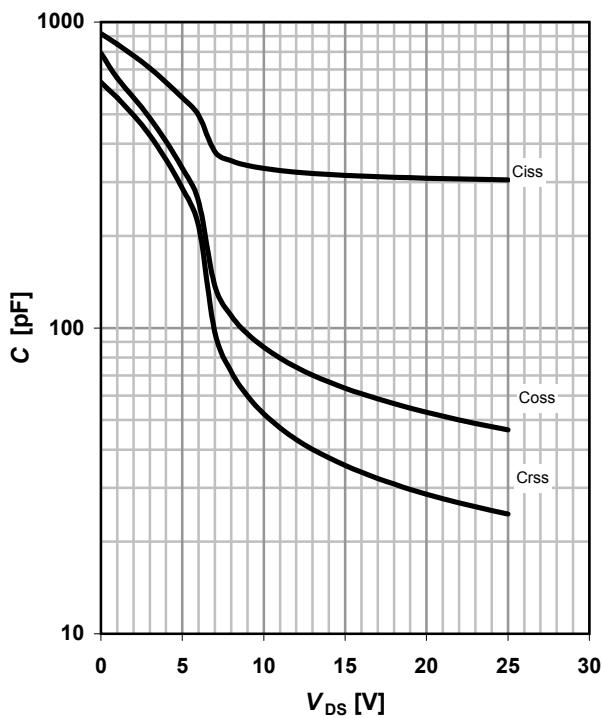
$V_{GS(th)} = f(T_j); V_{DS} = 3 \text{ V}; I_D = 400 \mu\text{A}$

parameter:  $I_D$



**11 Typ. Capacitances**

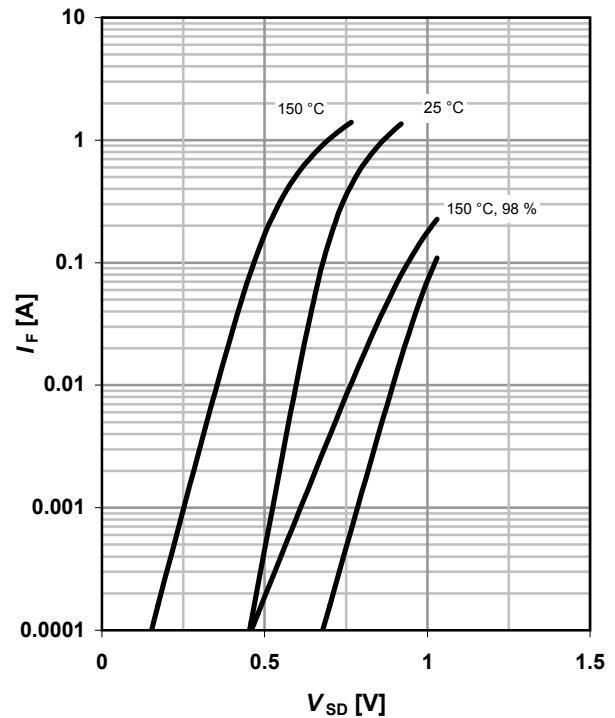
$C = f(V_{DS}); V_{GS} = -3 \text{ V}; f = 1 \text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

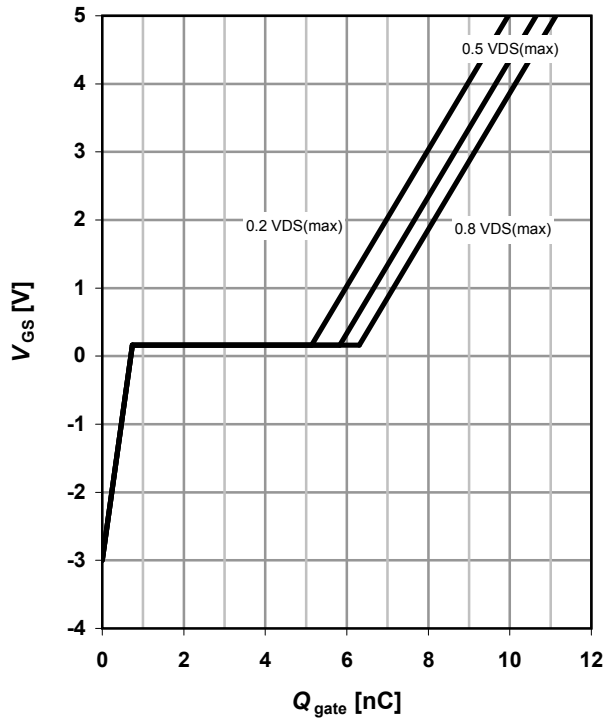
parameter:  $T_j$



**14 Typ. gate charge**

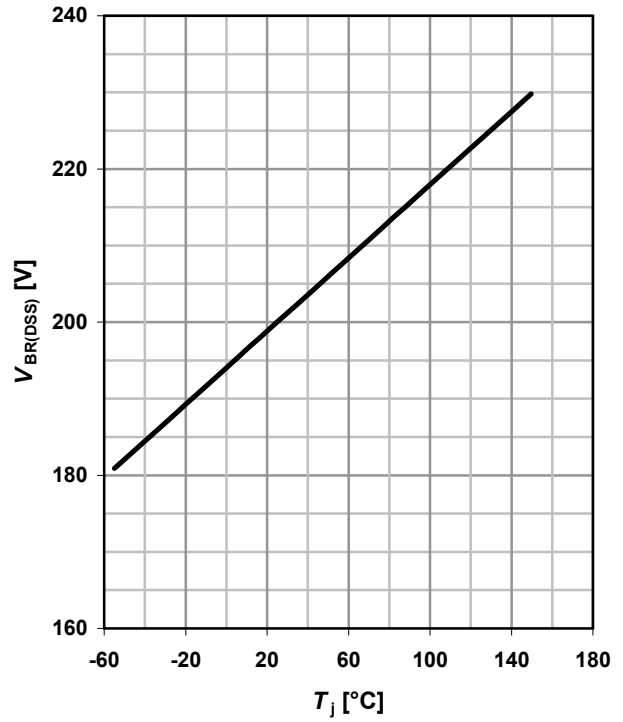
$V_{GS}=f(Q_{gate}); I_D=0.5\text{ A pulsed}$

parameter:  $V_{DD}$

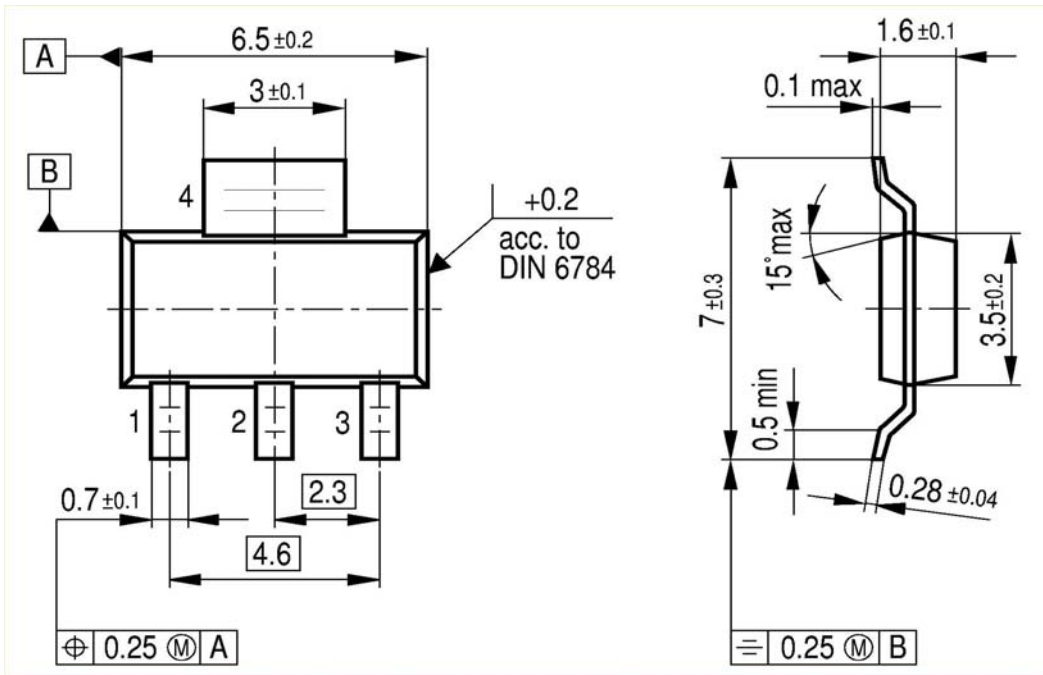


**15 Drain-source breakdown voltage**

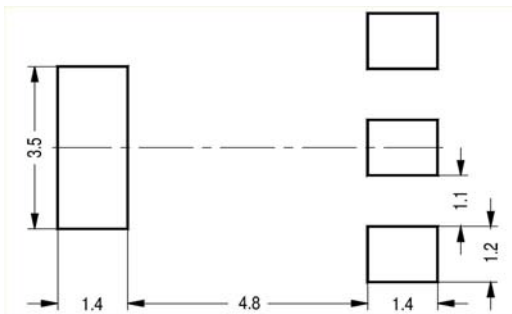
$V_{BR(DSS)}=f(T_j); I_D=250\text{ }\mu\text{A}$



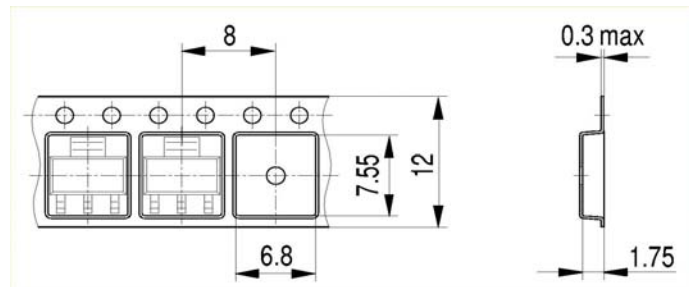
Package Outline:



Footprint:



Packaging:





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